

# RM4 - RM4Z

**PRV : 100 - 400 Volts**  
**Io : 1.7 Ampere**

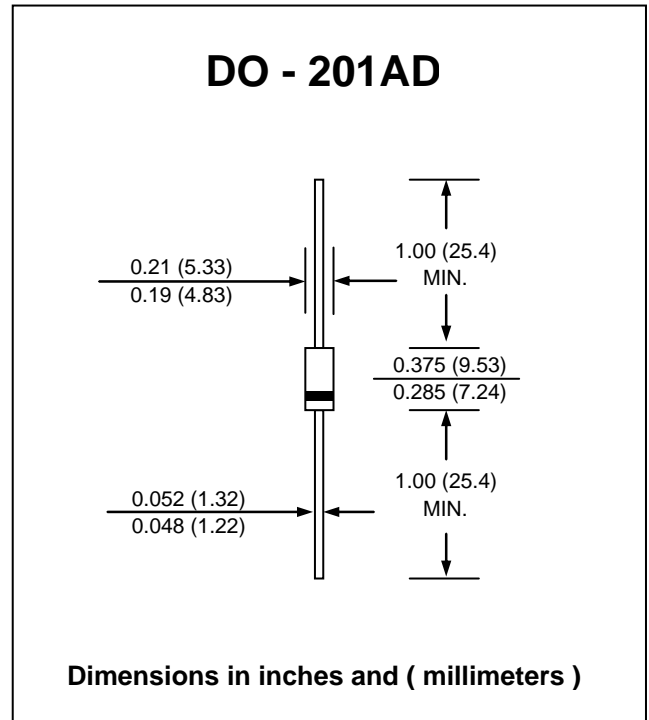
**FEATURES :**

- \* High current capability
- \* High surge current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* **Pb / RoHS Free**

**MECHANICAL DATA :**

- \* Case : DO-201AD Molded plastic
- \* Epoxy : UL94V-O rate flame retardant
- \* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 1.21 grams

# SILICON RECTIFIER DIODES



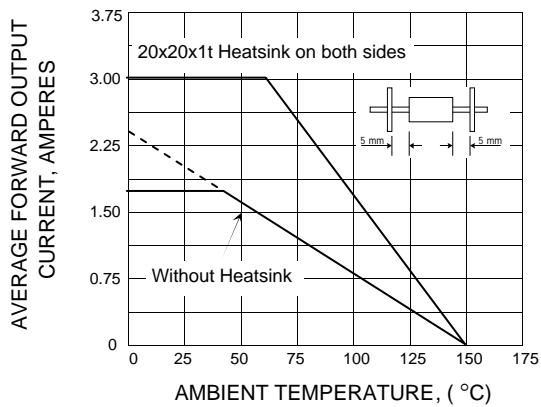
**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Rating at 25 °C ambient temperature unless otherwise specific.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

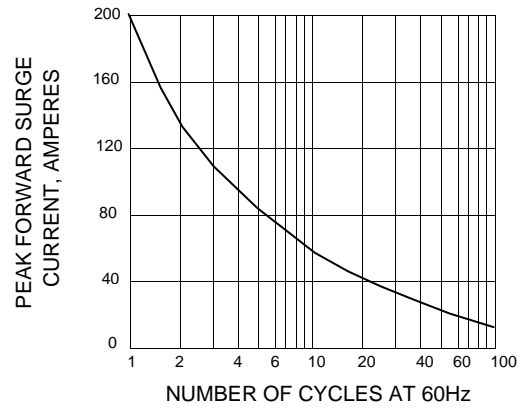
RATING	SYMBOL	RM4Y	RM4Z	RM4	UNIT
Maximum Reverse Voltage	$V_{RM}$	100	200	400	V
Maximum Peak Reverse Surge Voltage	$V_{RSM}$	150	250	450	V
Maximum Average Forward Current	$I_{F(AV)}$	1.7 (3.0 A is with Heatsink)			A
Maximum Peak Forward Surge Current Half-cycle Sine wave, 50 Hz, Single Shot	$I_{FSM}$	200			A
Maximum Forward Voltage at $I_F = 3.0 A$	$V_F$	0.95			V
Maximum Reverse Current $T_a = 25\text{ }^\circ\text{C}$ at $V_R = V_{Rmax}$ . $T_a = 150\text{ }^\circ\text{C}$	$I_R$	10			$\mu\text{A}$
	$I_{R(H)}$	50			$\mu\text{A}$
Junction Temperature Range	$T_J$	- 40 to + 150			$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	- 40 to + 150			$^\circ\text{C}$

## RATING AND CHARACTERISTIC CURVES ( RM4 - RM4Z )

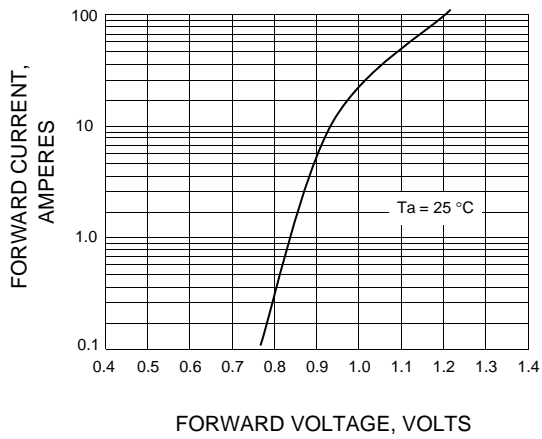
**FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS**

